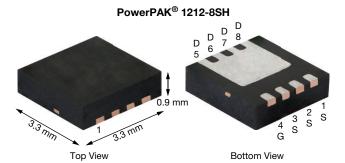
SiSH116DN

www.vishay.com

Vishay Siliconix

N-Channel 40 V (D-S) Fast Switching MOSFET



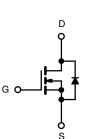
PRODUCT SUMMARY 40 V_{DS} (V) $R_{DS(on)}$ max. (Ω) at V_{GS} = 10 V 0.0078 $R_{DS(on)}$ max. (Ω) at V_{GS} = 4.5 V 0.0100 Qg typ. (nC) 15 $I_D(A)$ 16.4 Configuration Single

FEATURES

- TrenchFET[®] power MOSFET
- PWM optimized
- 100 % R_q tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

APPLICATIONS

- Synchronous rectification
- Intermediate switch
- Synchronous buck



N-Channel MOSFET

ORDERING INFORMATION	
Package	PowerPAK 1212-8
Lead (Pb)-free and halogen-free	SiSH116DN-T1-GE3

ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless	otherwise no	ted)			
PARAMETER		SYMBOL	10 s	STEADY STATE	UNIT	
Drain-source voltage		V _{DS}	40	40	V	
Gate-source voltage		V _{GS}	± 20	± 20	v	
Continuous drain surrent (T 150 °C) à	T _A = 25 °C	I _D	16.4	10.5		
Continuous drain current (T _J = 150 °C) ^a	T _A = 70 °C		13.1	8.4		
Pulsed drain current		I _{DM}	60	60	А	
Continuous source current (diode conduction) ^a		I _S	3.2	1.3		
Avalanche current		I _{AS}	15	15		
Avalanche energy	L = 0 1 mH	E _{AS}	11	11	mJ	
Mauianua a aura dia sia stiana 8	T _A = 25 °C	PD	3.8	1.5	14/	
Maximum power dissipation ^a	T _A = 70 °C		2	0.8	W	
Operating junction and storage temperature range		T _J , T _{stg}	-55 to +150		°C	
Soldering recommendations (peak temperature) ^{b, c}			20			

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT
Maximum junction-to-ambient ^a	t ≤ 10 s	Р	24	33	
Maximum junction-to-ambient ~	Steady state	R _{thJA}	65	81	°C/W
Maximum junction-to-case (drain)	Steady state	R _{thJC}	1.9	2.4	

Notes

a. Surface mounted on 1" x 1" FR4 board

See solder profile (<u>www.vishay.com/doc?73257</u>). The PowerPAK 1212-8SH is a leadless package within the PowerPAK 1212-8 package family. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection b.

c. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components

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1 For technical questions, contact: pmostechsupport@vishay.com

RoHS COMPLIANT HALOGEN

FREE

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SiSH116DN

Vishay Siliconix

SPECIFICATIONS (T _J = 25 °C PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
	STIMBUL	TEST CONDITIONS	IVIIN.	TTP.	IVIAA.	UNIT	
Static			·				
Gate threshold voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = 250 \ \mu A$	1.5	-	2.5	V	
Gate-body leakage	kage I_{GSS} $V_{DS} = 0 V, V_{GS} = \pm 20 V$		-	-	± 100	nA	
		V _{DS} = 40 V, V _{GS} = 0 V		1			
Zero gate voltage drain current	IDSS	V_{DS} = 40 V, V_{GS} = 0 V, T_{J} = 55 °C	-	-	5	μA	
On-state drain current ^a	I _{D(on)}	$V_{DS} \geq 5 \text{ V}, V_{GS} = 10 \text{ V}$	40	-	-	А	
		V _{GS} = 10 V, I _D = 16.4 A	-	0.0065	0.0078	Ω	
Drain-source on-state resistance ^a	R _{DS(on)}	V _{GS} = 4.5 V, I _D = 14.5 A	-	0.0083	0.0100		
Forward transconductance a	g _{fs}	V _{DS} = 15 V, I _D = 16.4 A	-	68	-	S	
Diode forward voltage ^a	V _{SD}	$I_{S} = 3.2 \text{ A}, V_{GS} = 0 \text{ V}$	-	0.8	1.2	V	
Dynamic ^b			•	•			
Total gate charge	Qg		-	15	23		
Gate-source charge	Q _{gs}	$V_{DS} = 20 \text{ V}, V_{GS} = 4.5 \text{ V}, I_D = 16.4 \text{ A}$	-	6.7	-	nC	
Gate-drain charge	Q _{gd}		-	5.1	-		
Gate resistance	Rg	f = 1 MHz	0.7	1.4	2.1	Ω	
Turn-on delay time	t _{d(on)}		-	10	15		
Rise time	t _r	$V_{DD} = 20 \text{ V}, \text{ R}_{L} = 20 \Omega$	-	10	15	ns	
Turn-off delay time	t _{d(off)}	$I_D \cong$ 1 A, V_{GEN} = 10 V, R_g = 6 Ω	-	36	55		
Fall time	t _f		-	10	15		
Source-drain reverse recovery time	t _{rr}		-	30	60		
Body diode reverse recovery charge	Q _{rr}	I _F = 3.2 A, di/dt = 100 A/µs	-	26	52	nc	

Notes

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %

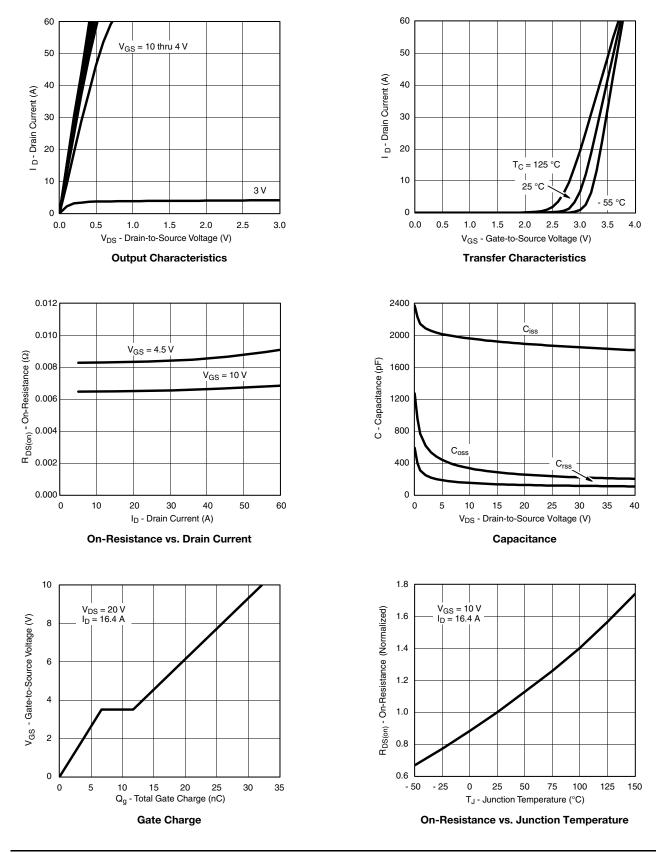
b. Guaranteed by design, not subject to production testing

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Document Number: 79240



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



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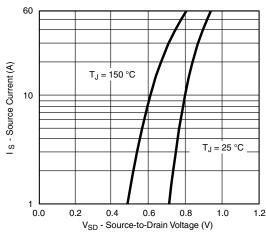
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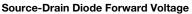
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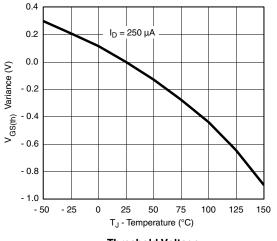
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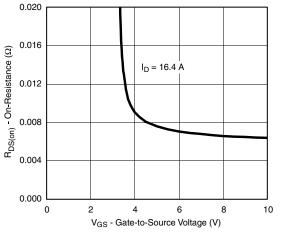
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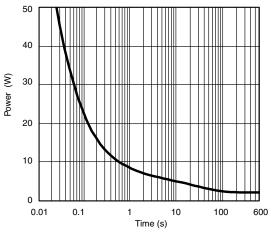




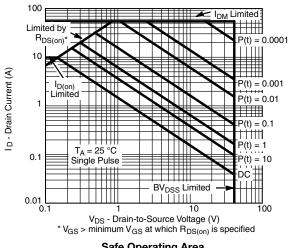




On-Resistance vs. Gate-to-Source Voltage



Single Pulse Power, Junction-to-Ambient



Safe Operating Area

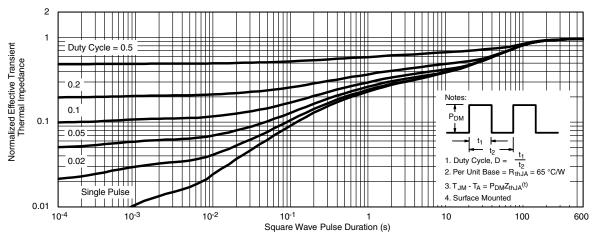
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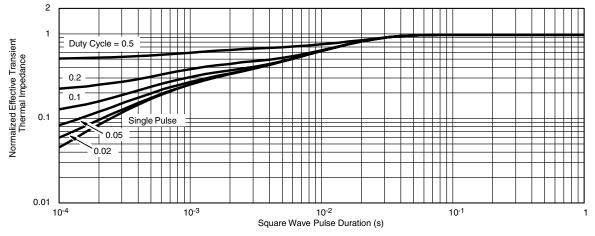
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Normalized Thermal Transient Impedance, Junction-to-Ambient

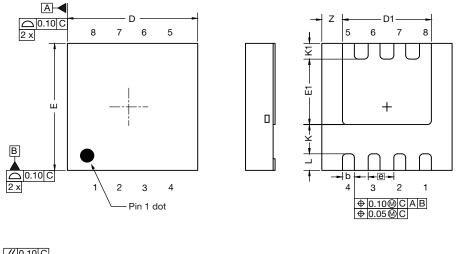


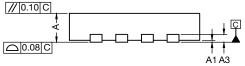
Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg?79240.



Case Outline for PowerPAK[®] 1212-SWLH and PowerPAK[®] 1212-8SH





DIM.	MILLIMETERS			INCHES			
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	
А	0.82	0.90	0.98	0.032	0.035	0.038	
A1	0.00	-	0.05	0.000	-	0.002	
A3	0.20 ref.			0.008 ref.			
b	0.25	0.30	0.35	0.010	0.012	0.014	
D	3.20	3.30	3.40	0.126	0.130	0.134	
D1	2.15	2.25	2.35	0.085	0.089	0.093	
E	3.20	3.30	3.40	0.126	0.130	0.134	
E1	1.60	1.70	1.80	0.063	0.067	0.071	
е	0.65 bsc.			0.026 bsc.			
К	0.76 ref.			0.030 ref.			
K1	0.41 ref.		0.016 ref.				
L	0.33	0.43	0.53	0.013	0.017	0.021	
Z	0.525 ref.			0.021 ref.			



RECOMMENDED MINIMUM PADS FOR PowerPAK[®] 1212-8 Single



Recommended Minimum Pads Dimensions in Inches/(mm)

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